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(71)Applicant : FUJI PHOTO FILM CO LTD

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(72)Inventor : SATO KENICHIRO

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## (54) RESIST COMPOSITION

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a resist composition which is suitably used in a super-microlithography process and other photofabrication processes such as manufacture of VLSIs and high capacity microchips and whose surface roughness in etching is reduced, and further a resist composition which has superior characteristics of sensitivity, resolving power, a profile, a pattern fall, a side lobe margin, roughness and fineness dependency, etc.

**SOLUTION:** The resist composition contains (A) a resin which has a partial structure having a hydroxyl group replaced with a hydrocarbon group, has 120 to 180° C glass transition temperature, is decomposed by an acid and has its dissolution rate in an alkaline developing solution increased, (B) a compound which generates an acid by irradiation with an active ray or radiation, and (C) a solvent.

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